PROCESS CPD04

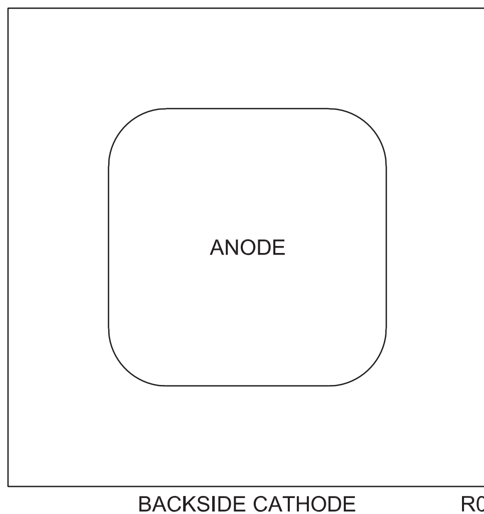
General Purpose Rectifier

500mA Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	26 x 26 MILS
Die Thickness	8.5 MILS
Anode Bonding Pad Area	14 x 14 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



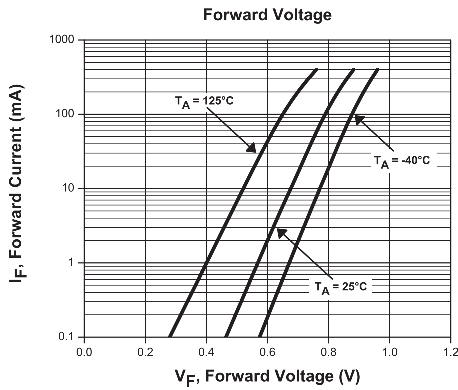
GROSS DIE PER 4 INCH WAFER
18,000

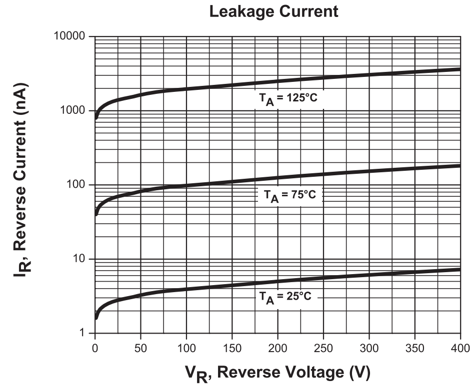
PRINCIPAL DEVICE TYPES
1N645 thru 1N649
CBRHD-02 Series

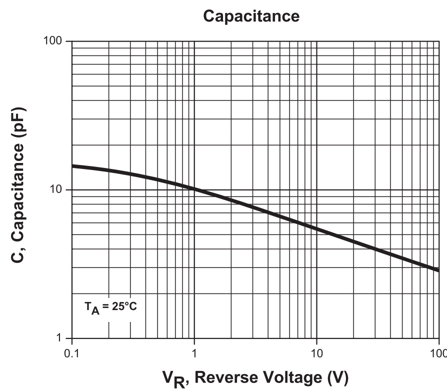
R4 (22-March 2010)

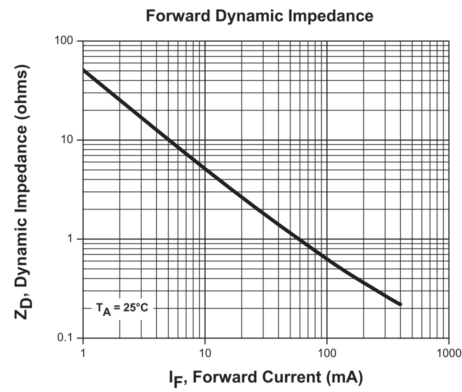
PROCESS CPD04

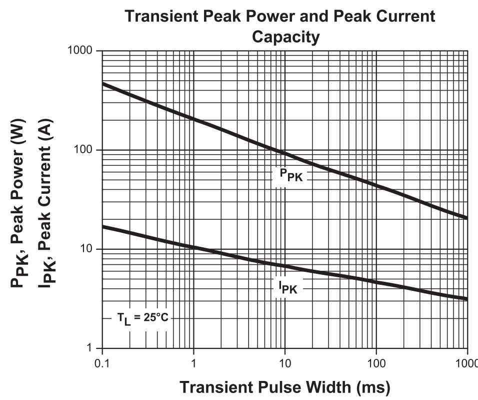
Typical Electrical Characteristics

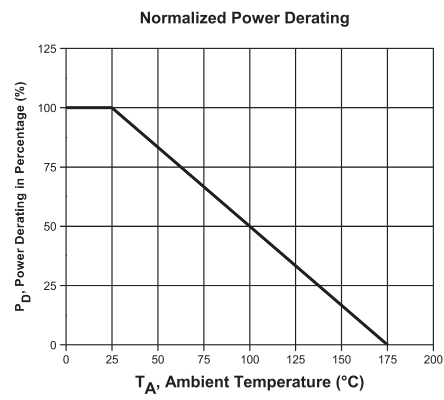












R4 (22-March 2010)